

KSA1220/1220A

Audio Frequency Power Amplifier High Frequency Power Amplifier

Complement to KSC2690/KSC2690A



PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

| Symbol | Parameter | | Ratings | Units | |
|--|--|------------|------------|-------|--|
| V _{CBO} | Collector-Base Voltage | : KSA1220 | - 120 | V | |
| | 11 41 | : KSA1220A | - 160 | V | |
| V _{CEO} | Collector-Emitter Voltage | : KSA1220 | - 120 | V | |
| | | : KSA1220A | - 160 | V | |
| V_{EBO} | Emitter-Base Voltage | | - 5 | V | |
| I _C | Collector Current (DC) | | - 1.2 | А | |
| I _{CP} | *Collector Current (Pulse) | | - 2.5 | А | |
| I _B | Base Current | | - 0.3 | А | |
| P _C | Collector Dissipation (T _a =25°C) | | 1.2 | W | |
| P _C P _C T _J | Collector Dissipation (T _C =25°C) | | 20 | W | |
| T _J | Junction Temperature | n M | 150 | °C | |
| T _{STG} | Storage Temperature | | - 55 ~ 150 | °C | |

^{*} PW≤10ms, Duty Cycle≤50%

Electrical Characteristics T_C=25°C unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|--------------------------------------|--|---|----------|------------|-------|-------|
| I _{CBO} | Collector Cut-off Current | $V_{CB} = -120V, I_{E} = 0$ | - 19 | 7 | - 1 | μΑ |
| I _{EBO} | Emitter Cut-off Current | $V_{EB} = -3V, I_{C} = 0$ | | -50.7 | - 1 | μΑ |
| h _{FE1} h _{FE2} | * DC Current Gain | $V_{CE} = -5V, I_{C} = -5mA$ $V_{CE} = -5V, I_{C} = -0.3A$ | 35 60 | 150 140 | 320 | |
| V _{CE} (sat) | * Collector-Emitter Saturation Voltage | $I_C = -1A$, $I_B = -0.2A$ | | - 0.4 | - 0.7 | V |
| V _{BE} (sat) | * Base-Emitter Saturation Voltage | $I_C = -1A, I_B = -0.2A$ | | - 1 | - 1.3 | V |
| f _T | Current Gain Bandwidth Product | $V_{CE} = -5V, I_{C} = -0.2A$ | | 175 | | MHz |
| C _{ob} | Output Capacitance | $V_{CB} = -10, I_{E} = 0$ f = 1MHz | | 26 | | pF |

^{*} Pulse Test: PW≤350μs, Duty Cycle≤2% Pulsed

h_{FE} Classification

| Classification | R | 0 | Y |
|------------------|----------|-----------|-----------|
| h _{FE2} | 60 ~ 120 | 100 ~ 200 | 160 ~ 320 |

Typical Characteristics

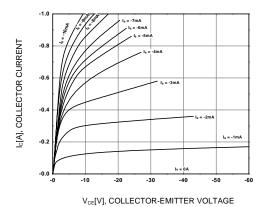


Figure 1. Static Characteristic

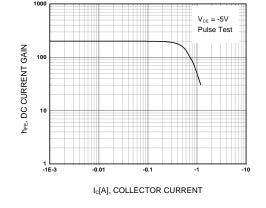


Figure 2. DC current Gain

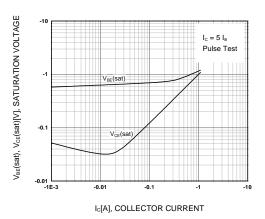


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

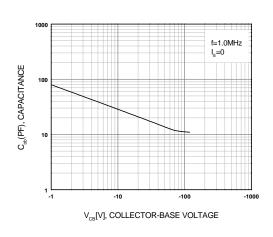


Figure 4. Collector Output Capacitance

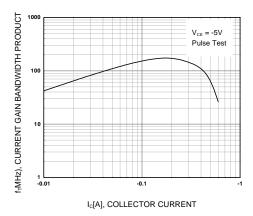


Figure 5. Current Gain Bandwidth Product

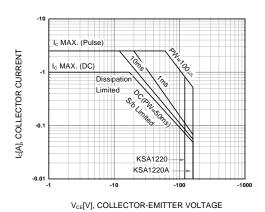


Figure 6. Safe Operating Area

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Typical Characteristics (Continued)

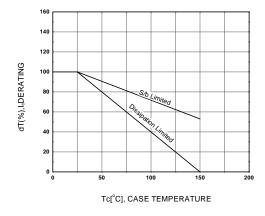


Figure 7. Derating Curve of Safe Operating Areas

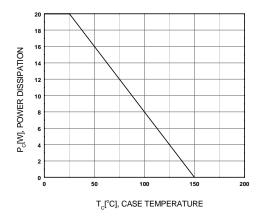
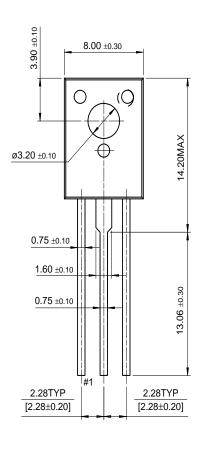
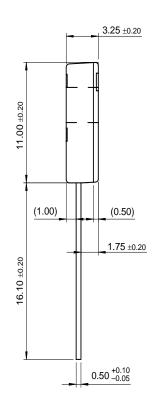


Figure 8. Power Derating

Package Demensions

TO-126







Dimensions in Millimeters

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